

30V Dual P-Channel Enhancement Mode MOSFET

Description

The PECN4805 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a load switch or in PWM applications.

General Features

- ◆ $V_{DS} = -30V$, $I_D = -8A$
 $R_{DS(ON)}(Typ.) = 17.5m\Omega$ @ $V_{GS} = -4.5V$
 $R_{DS(ON)}(Typ.) = 16.5m\Omega$ @ $V_{GS} = -10V$
- ◆ High power and current handling capability
- ◆ Lead free product is acquired
- ◆ Surface mount package

Application

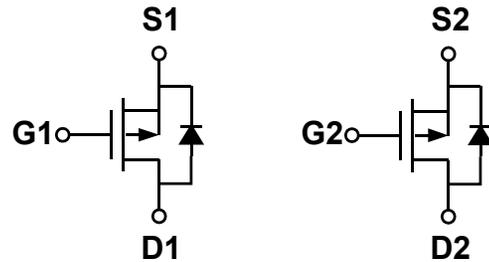
- ◆ PWM applications
- ◆ Load switch

Package

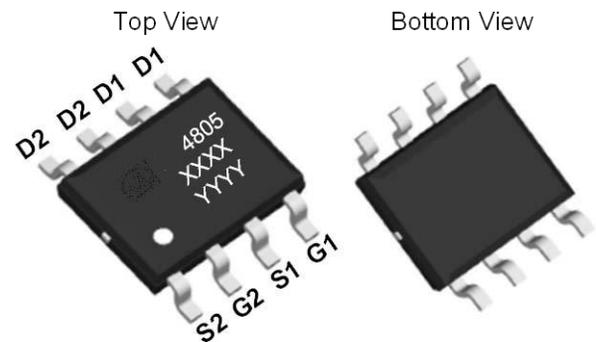
- ◆ SOP-8

100% UIS TESTED!
100% ΔV_{ds} TESTED!

Schematic diagram



Marking and pin assignment



XXXX is the date code ,
 YYY is the Quality Code.



Ordering Information

| Part Number | Storage Temperature | Package | Devices Per Reel |
|------------------|---------------------|---------|------------------|
| PECN4805S R-G | -55°C to +150°C | SOP-8 | 4000 |

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

| parameter | symbol | limit | unit | |
|--|----------|--------------------|------|---|
| Drain-source voltage | V_{DS} | -30 | V | |
| Gate-source voltage | V_{GS} | ± 20 | V | |
| Drain Current-Continuous (Silicon Limited) | I_D | $T_A = 25^\circ C$ | -8 | A |
| | | $T_A = 75^\circ C$ | -6 | |
| Pulsed Drain Current (Package Limited) | I_{DM} | -32 | A | |
| Maximum power dissipation | P_D | $T_A = 25^\circ C$ | 2 | W |
| | | $T_A = 75^\circ C$ | 1.3 | |
| Operating junction Temperature range | T_j | -55—150 | °C | |

Electrical Characteristics (TA=25°C unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|--------------|---|------|------|-----------|------------|
| Static Characteristics | | | | | | |
| Drain-source breakdown voltage | BV_{DSS} | $V_{GS}=0V, I_D=-250\mu A$ | -30 | - | - | V |
| Zero gate voltage drain current | I_{DSS} | $V_{DS}=-30V, V_{GS}=0V$ | - | - | 1 | μA |
| | | $T_J=85^\circ C$ | - | - | 30 | |
| Gate Leakage Current | I_{GSS} | $V_{DS}=0V, V_{GS}=\pm 20V$ | - | - | ± 100 | nA |
| Gate threshold voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=-250\mu A$ | -1.2 | -1.6 | -2.5 | V |
| Drain-source on-state resistance ¹ | $R_{DS(ON)}$ | $V_{GS}=-10V, I_D=-8A$ | - | 16.5 | 20 | m Ω |
| | | $V_{GS}=-4.5V, I_D=-7A$ | - | 17.5 | 25 | |
| On Status Drain Current | $I_{D(ON)}$ | $V_{DS}=-15V, V_{GS}=-10V$ | 8 | - | - | A |
| Diode Characteristics | | | | | | |
| Diode Forward Voltage | V_{SD} | $I_{SD}=-8A, V_{GS}=0V$ | - | -0.8 | -1.3 | V |
| Diode Continuous Forward Current | I_S | | - | -8 | - | A |
| Reverse Recovery Time | t_{rr} | $I_F=-8A,$ $dI/dt=-100A/\mu s$ | - | 24 | - | ns |
| Reverse Recovery Charge | Q_{rr} | | - | 16 | - | nC |
| Dynamic Characteristics | | | | | | |
| Gate Resistance | R_G | $V_{GS}=0V, V_{DS}=0V, f=1MHz$ | - | 0.65 | - | Ω |
| IPECNut capacitance | C_{ISS} | $V_{GS}=0V, V_{DS}=-15V$ $f=1.0MHz$ | - | 1360 | - | pF |
| Output capacitance | C_{OSS} | | - | 250 | - | |
| Reverse transfer capacitance | C_{RSS} | | - | 210 | - | |
| Turn-on delay time | $t_{D(ON)}$ | $V_{GS}=-10V, V_{DD}=-30V,$ $R_L=3\Omega, I_D=1A, R_G=2.5\Omega$ | - | 9 | - | ns |
| Turn-on Rise time | t_r | | - | 10 | - | |
| Turn-off delay time | $t_{D(OFF)}$ | | - | 50 | - | |
| Turn-off Fall time | t_f | | - | 20 | - | |
| Total gate charge | Q_g | $V_{GS}=-10V, I_D=-8A$ $V_{DS}=-15V$ | - | 31 | - | nC |
| Gate-source charge | Q_{gs} | | - | 3 | - | |
| Gate-drain charge | Q_{gd} | | - | 9 | - | |

Thermal Characteristics

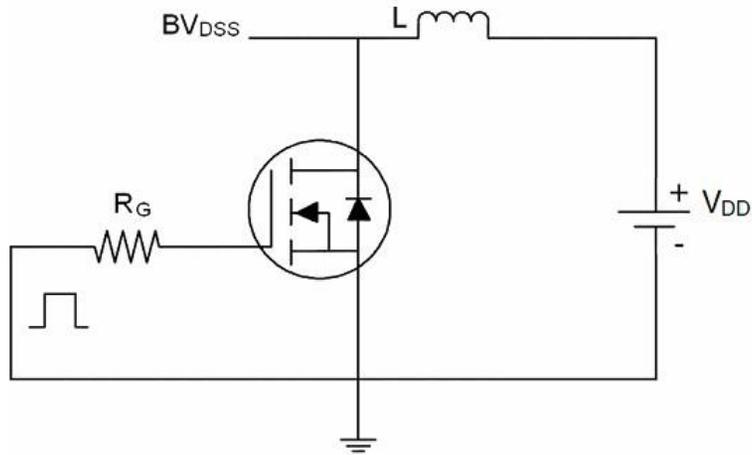
| Parameter | Symbol | Typ | Max | Unit |
|--|--------------|-----|-----|--------------|
| Maximum Junction-to-Ambient ^A | $\leq 10s$ | 33 | 40 | $^\circ C/W$ |
| Maximum Junction-to-Ambient ^A | Steady-State | | | |
| Maximum Junction-to-Lead ^B | Steady-State | 16 | 24 | |

A: The value of R_{qJA} is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ C$. The value in any given application depends on the user's specific board design. The current rating is based on the $t \leq 10s$ thermal resistance rating.

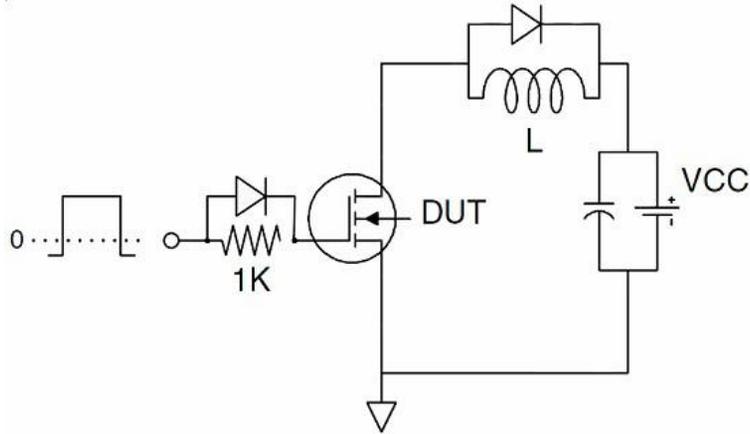
B: The R_{qJA} is the sum of the thermal impedance from junction to lead R_{qJL} and lead to ambient.

Test Circuit:

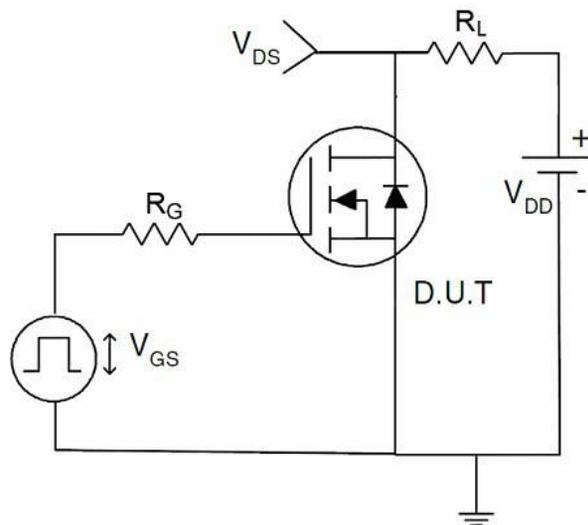
1 、 EAS Test Circuit



2 、 Gate Charge Test Circuit

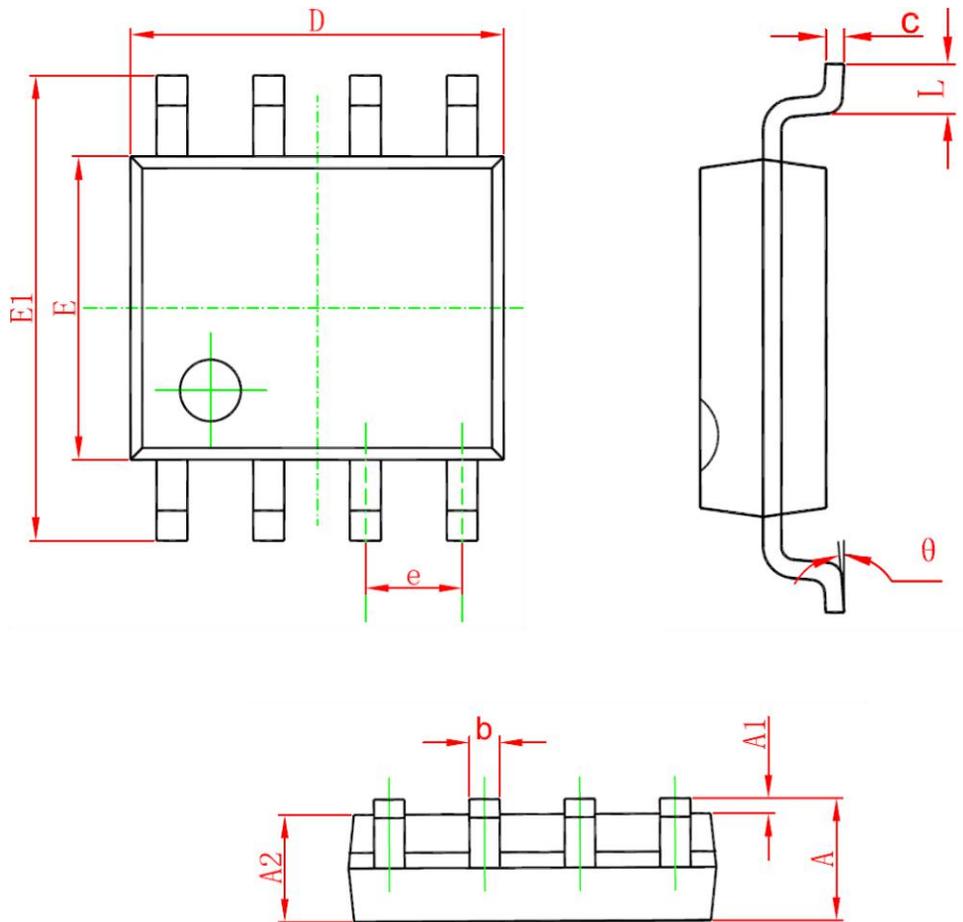


3 、 Switch Time Test Circuit



Package Information

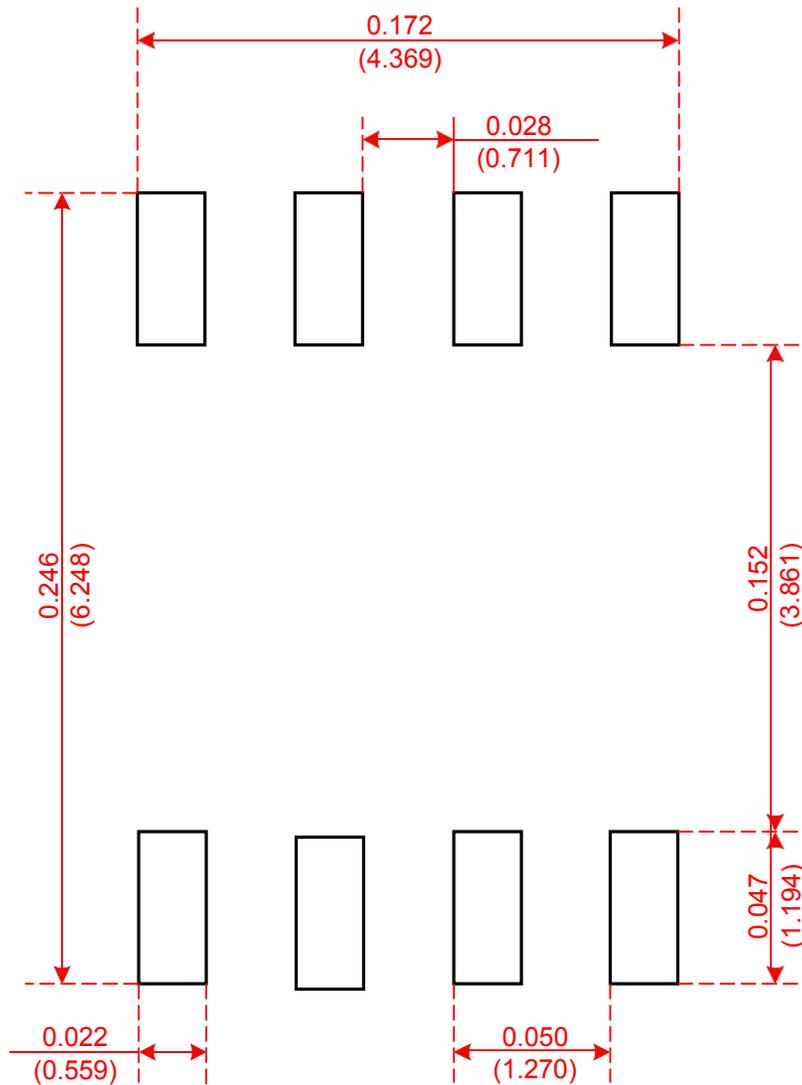
- SOP-8



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min | Max | Min | Max |
| A | 1.350 | 1.750 | 0.053 | 0.069 |
| A1 | 0.100 | 0.250 | 0.004 | 0.010 |
| A2 | 1.350 | 1.550 | 0.053 | 0.061 |
| b | 0.330 | 0.510 | 0.013 | 0.020 |
| c | 0.170 | 0.250 | 0.006 | 0.010 |
| D | 4.700 | 5.100 | 0.185 | 0.200 |
| E | 3.800 | 4.000 | 0.150 | 0.157 |
| E1 | 5.800 | 6.200 | 0.228 | 0.244 |
| e | 1.270 (BSC) | | 0.050 (BSC) | |
| L | 0.400 | 1.270 | 0.016 | 0.050 |
| θ | 0° | 8° | 0° | 8° |

Recommended Minimum Pads

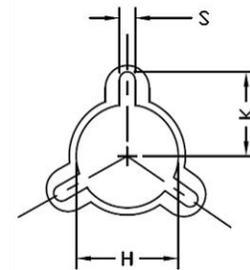
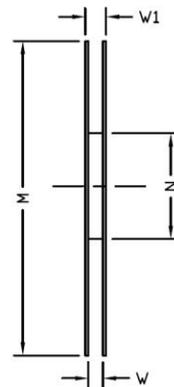
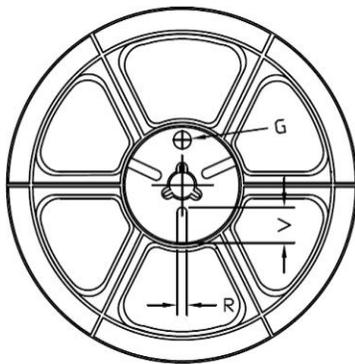
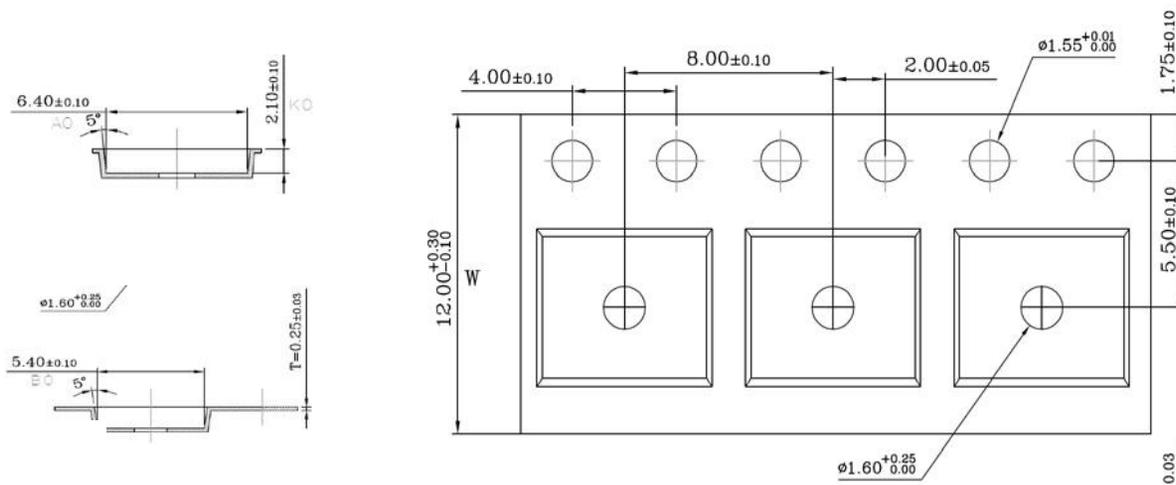
- SOP-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

Tape and Reel

- SOP-8



| Tape Size | Reel Size | M | N | W | W1 | H | K | S | G | R | V |
|-----------|-----------|------------------|-----------------|----------------|----------------|----------------|------|---------------|---|---|---|
| 12mm | Φ330 | Φ330.00 ±0.50 | Φ97.00 ±0.30 | 13.00 ±0.30 | 17.40 ±1.00 | Φ13.00 ±0.5 | 10.6 | 2.00 ±0.50 | — | — | — |

Unit Per Reel:
4000pcs

